

L Number	Hits	Search Text	DB	Time stamp
1	3877	((257/664) or (257/700) or (257/728) or (438/10) or (438/11) or (438/13) or (438/14) or (438/17) or (438/18)).CCLS.	USPAT; US-PGPUB	2004/01/08 20:15
2	29	((257/664) or (257/700) or (257/728) or (438/10) or (438/11) or (438/13) or (438/14) or (438/17) or (438/18)).CCLS.) and (input output impedance) near15 (match matching) and (power adj transistor high adj voltage near2 transistor power adj device)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 20:18
3	126	(input output impedance) near15 (match matching) and (power adj transistor high adj voltage near2 transistor power adj device)	EPO; JPO; DERWENT; IBM_TDB	2004/01/08 20:19
-	1630	power adj transistor.ti,ab. and amplifier.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/08 18:04
-	222	power adj transistor.ti. and amplifier.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 08:48
-	23	power adj transistor.ti. and amplifier.ti. and (rf or radio adj frequency).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 10:05
-	126	power adj transistor.ti. and (rf or radio adj frequency).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 10:07
-	87	power adj transistor.ti. and (rf or radio adj frequency).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 10:30
-	220	internal adj matching	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 10:31
-	48	internal adj matching with transistor.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 10:34
-	0	(internal adj matching with transistor.ti,ab.) and ldmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 10:35
-	0	(internal adj matching with transistor.ti,ab.) and ldmosfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 10:35
-	0	(internal adj matching with transistor.ti,ab.) and mosfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 10:35
-	12	(internal adj matching with transistor.ti,ab.) and field adj effect adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 10:35

-	0	JP-2001024148 JP-05218102 JP-04321308 JP-01283951 JP-02005459 JP-01199436 JP-63086904 JP-55091148	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 12:12
-	14	JP-05218102\$-\$.did. JP-04321308\$-\$.did. JP-01283951\$-\$.did. JP-02005459\$-\$.did. JP-01199436\$-\$.did. JP-63086904\$-\$.did. JP-55091148\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 12:13
-	10	((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 12:14
-	4	EP-680141\$-\$.did. JP-01050602\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 12:15
-	0	((JP-05218102\$-\$.did. JP-04321308\$-\$.did. JP-01283951\$-\$.did. JP-02005459\$-\$.did. JP-01199436\$-\$.did. JP-63086904\$-\$.did. JP-55091148\$-\$.did.) or (((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608"))).PN.) or (EP-680141\$-\$.did. JP-01050602\$-\$.did. )) and substrate and transistor and input adj matching and lead and wir\$3 and impedance and (die or dice or chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 12:17
-	0	((JP-05218102\$-\$.did. JP-04321308\$-\$.did. JP-01283951\$-\$.did. JP-02005459\$-\$.did. JP-01199436\$-\$.did. JP-63086904\$-\$.did. JP-55091148\$-\$.did.) or (((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608"))).PN.) or (EP-680141\$-\$.did. JP-01050602\$-\$.did. )) and substrate and transistor and input adj matching and lead and wir\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 12:17
-	8	((JP-05218102\$-\$.did. JP-04321308\$-\$.did. JP-01283951\$-\$.did. JP-02005459\$-\$.did. JP-01199436\$-\$.did. JP-63086904\$-\$.did. JP-55091148\$-\$.did.) or (((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608"))).PN.) or (EP-680141\$-\$.did. JP-01050602\$-\$.did. )) and substrate and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 12:17

-	8	((JP-05218102\$-\$\$.did. JP-04321308\$-\$\$.did. JP-01283951\$-\$\$.did. JP-02005459\$-\$\$.did. JP-01199436\$-\$\$.did. JP-63086904\$-\$\$.did. JP-55091148\$-\$\$.did.) or (((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608"))).PN.) or (EP-680141\$-\$\$.did. JP-01050602\$-\$\$.did. )) and substrate and transistor and match\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 12:17
-	2	((JP-05218102\$-\$\$.did. JP-04321308\$-\$\$.did. JP-01283951\$-\$\$.did. JP-02005459\$-\$\$.did. JP-01199436\$-\$\$.did. JP-63086904\$-\$\$.did. JP-55091148\$-\$\$.did.) or (((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608"))).PN.) or (EP-680141\$-\$\$.did. JP-01050602\$-\$\$.did. )) and substrate and transistor and match\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 12:18
-	2	((JP-05218102\$-\$\$.did. JP-04321308\$-\$\$.did. JP-01283951\$-\$\$.did. JP-02005459\$-\$\$.did. JP-01199436\$-\$\$.did. JP-63086904\$-\$\$.did. JP-55091148\$-\$\$.did.) or (((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608"))).PN.) or (EP-680141\$-\$\$.did. JP-01050602\$-\$\$.did. )) and substrate and transistor and match\$3 and lead\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 12:18
-	2	((JP-05218102\$-\$\$.did. JP-04321308\$-\$\$.did. JP-01283951\$-\$\$.did. JP-02005459\$-\$\$.did. JP-01199436\$-\$\$.did. JP-63086904\$-\$\$.did. JP-55091148\$-\$\$.did.) or (((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608"))).PN.) or (EP-680141\$-\$\$.did. JP-01050602\$-\$\$.did. )) and substrate and transistor and match\$3 and lead\$1 and wir\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 13:41
-	1	((JP-05218102\$-\$\$.did. JP-04321308\$-\$\$.did. JP-01283951\$-\$\$.did. JP-02005459\$-\$\$.did. JP-01199436\$-\$\$.did. JP-63086904\$-\$\$.did. JP-55091148\$-\$\$.did.) or (((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608"))).PN.) or (EP-680141\$-\$\$.did. JP-01050602\$-\$\$.did. )) and substrate and transistor and match\$3 and lead\$1 and wir\$3 and impedance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 13:43
-	4393	((JP-05218102\$-\$\$.did. JP-04321308\$-\$\$.did. JP-01283951\$-\$\$.did. JP-02005459\$-\$\$.did. JP-01199436\$-\$\$.did. JP-63086904\$-\$\$.did. JP-55091148\$-\$\$.did.) or (((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608"))).PN.) or (EP-680141\$-\$\$.did. JP-01050602\$-\$\$.did. )) and (wir\$3 with impedance) (wir\$3 with impedance).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 13:43
-	207	((JP-05218102\$-\$\$.did. JP-04321308\$-\$\$.did. JP-01283951\$-\$\$.did. JP-02005459\$-\$\$.did. JP-01199436\$-\$\$.did. JP-63086904\$-\$\$.did. JP-55091148\$-\$\$.did.) or (((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608"))).PN.) or (EP-680141\$-\$\$.did. JP-01050602\$-\$\$.did. )) and (wir\$3 with impedance) (wir\$3 with impedance).ti,ab. and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 13:44

-	13	(bonding adj2 wir\$3 near5 impedance).ti,ab. and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 16:39
-	3	5371405.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 16:40
-	2	6281756.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 16:42
-	545	257/664	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 16:43
-	27	(JP-05218102\$-\$.did. JP-04321308\$-\$.did. JP-01283951\$-\$.did. JP-02005459\$-\$.did. JP-01199436\$-\$.did. JP-63086904\$-\$.did. JP-55091148\$-\$.did.) or (((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608")).PN.) or (EP-680141\$-\$.did. JP-01050602\$-\$.did. )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 16:44
-	0	jp-404048756\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 16:45
-	2	jp-04048756\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 16:48
-	1768	257/700	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 16:48
-	742	257/728	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 16:48
-	16	(257/664 or 257/700 or 257/728) and wir\$3 and substrate and power adj transistor and matching and impedance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 16:50
-	212	trench same gate same high adj voltage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/11 07:57
-	46	trench same gate same high adj voltage and field adj effect adj transistor and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/11 07:58
-	6	(trench.ti,ab. same gate same high adj voltage) and field adj effect adj transistor and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/11 07:59

-	2937	257/664 or 257/700 or 257/728	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 15:50
-	33	(257/664 or 257/700 or 257/728) and impedance near12 (tailor or tailored or adjust or adjustment)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 15:52
-	8	(257/664 or 257/700 or 257/728) and impedance near12 (tailor or tailored or adjust or adjustment) and (length or number) near12 wire	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 16:16
-	325	impedance near12 (tailor or tailored or adjust or adjustment) and (length or number) near12 wire	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 16:17
-	227	impedance near6 (tailor or tailored or adjust or adjustment) and (length or number) near6 wire	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 16:18
-	11	impedance near4 (tailor or tailored or adjust or adjustment) and (length or number) near4 wire and (variance or rms or root-mean-square or root adj mean adj square)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 16:19
-	2	("5371405").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 09:33
-	2	("6281756").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 09:38
-	0	("jp-4048756").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 09:38
-	0	jp-04048756	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 09:38
-	2	jp-04048756\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 09:38
-	1135	impedance near6 (match or matching or matched) near6 (wire or wiring)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 17:10
-	488	impedance adj matching near6 (wire or wiring)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 17:10
-	47	impedance adj matching near6 (wire or wiring) and (257/\$6.ccls. or 438/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 19:45

-	0	trimmable near2 (bonding or bond) near2 (wire or wiring)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 19:46
-	5	trimmable near12 (bonding or bond) near12 (wire or wiring)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 19:58
-	8	trimmable adj (resistance or resistor) near3 laser and (257/\$6.ccls. or 438/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 20:08
-	0	trimmable adj (resistance or resistor) near6 laser near6 (wire or wiring) and (257/\$6.ccls. or 438/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 20:04
-	5	trimmable adj (resistance or resistor) near6 (wire or wiring) and (257/\$6.ccls. or 438/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 20:04
-	20	trimmable adj (resistance or resistor) near3 laser.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 20:19
-	0	trimmable adj (resistance or resistor) near3 wire.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 20:19
-	0	trimmable adj wire.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 20:19
-	8365	(trimmablele adj resistor-switch or rs) near12 (wire or wiring)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/13 08:05
-	92	(trimmable adj resistor-switch or rs) near12 (wire or wiring) near12 (testing or test)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/13 08:11
-	0	(trimmable adj resistor-switch or rs) near12 (wire or wiring) near12 (testing or test) near12 impedance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/13 08:11
-	27	(trimmable adj resistor-switch or rs) near12 (wire or wiring) near12 (testing or test) and (438/\$6.ccls. or 257/\$6.ccls. or 324/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/13 08:33
-	287	(secure or securing) near3 (die or chip) near3 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/23 15:00
-	2	(secure or securing) near3 (die or chip) near3 substrate and (test or testing or measure or measuring) near3 performance adj characteristic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/23 15:02

-	2	(secure or securing) near3 (die or chip) near3 substrate and (test or testing or measure or measuring or determine or determining) near3 performance adj characteristic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/23 15:09
-	8	impedance near3 adjust same length near3 wire	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/23 15:09
-	37	(resistance or impedance) near3 (adjust or adjustment) same (length near3 (wire or wiring))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/23 15:10
-	0	(resistance or impedance) near3 (adjust or adjustment) near12 (length near3 (wire or wiring)) and (die or chip) near12 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/23 15:12
-	1	(resistance or impedance) near3 (adjust or adjustment) near12 (length near3 (wire or wiring)) and (die or chip) same substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/23 15:12
-	27	(US-6177801-\$ or US-6084946-\$ or US-6060778-\$ or US-5978449-\$ or US-5864602-\$ or US-5862040-\$ or US-5578931-\$ or US-5528156-\$ or US-5633595-\$ or US-5600240-\$ or US-6389109-\$ or US-5592099-\$ or US-5589780-\$ or US-6417672-\$ or US-6385297-\$ or US-6225811-\$ or US-4320338-\$ or US-3660249-\$ or US-5485093-\$ or US-5250908-\$ or US-4495465-\$ or US-6456088-\$).did. or (US-20020105336-\$).did. or (EP-103971-\$).did. or (JP-01282476-\$ or JP-62272550-\$ or JP-04102345-\$).did.	USPAT; US-PGPUB; EPO; JPO;	2003/01/23 15:44
-	62	(trimmable adj resistor-switch or rs) near12 (wire or wiring) near12 (testing or test) not (438/\$6.ccls. or 257/\$6.ccls. or 324/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/23 16:36
-	4168	((438/10) or (438/11) or (438/13) or (438/17) or (438/18)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/23 16:37
-	2	((438/10) or (438/11) or (438/13) or (438/17) or (438/18)).CCLS.) and impedance near3 match\$3 and power adj2 (transistor or FET or MOSFET or NMOSFET or CMOSFET or PMOSFET or VMOSFET or UMOSFET or DMOSFET or field adj effect adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/23 16:39
-	0	(wire or wiring) near6 (varied or varying) near6 number near12 impedance and power.ti,ab. and (die or chip) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/23 19:05
-	28	power adj2 (semiconductor or transistor).ti,ab. and impedance near12 (adjust or adjusting or match or matching) near12 (wire or wiring or lead or leads)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/24 09:45

-	15	(US-5973567-\$ or US-5880517-\$ or US-5696466-\$ or US-5552636-\$ or US-5446959-\$ or US-5023189-\$ or US-4042952-\$ or US-6501159-\$ or US-6177834-\$).did. or (US-20020134993-\$ or US-20010038310-\$ or US-20010004115-\$).did. or (JP-11238851-\$).did. or (EP-1237189-\$ or US-6177834-\$).did.	USPAT; US-PGPUB; JPO; DERWENT	2003/01/24 08:45
-	437	interconnect\$3.ti,ab. and semiconductor.ti,ab. and line adj width	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/24 09:47
-	34	(interconnect\$3.ti,ab. and semiconductor.ti,ab. and line adj width) and impedance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/24 10:27
-	953	(438/14).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/24 10:27
-	12	((438/14).CCLS.) and impedance near12 (wire or wiring or interconnect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/24 10:38
-	0	impedance near3 matching adj circuit near12 (number near3 wires)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/24 10:41
-	382	(324/719).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/24 10:45
-	120	impedance near6 wires near6 number	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/24 10:46
-	0	((324/719).CCLS.) and (impedance near6 wires near6 number)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/24 10:46
-	6	adjust\$3 near6 impedance near6 wires near6 number	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/24 10:47
-	7	adjust\$4 near6 impedance near6 wires near6 number	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/24 11:48
-	2	(("5023189") or ("6331804")).PN.	USPAT	2003/01/24 11:49
-	2	(US-6331804-\$ or US-5023189-\$).did.	USPAT	2003/01/24 11:49
-	18	jp-0600615\$-\$).did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/24 11:50
-	8	jp-0600615\$-\$).did.	JPO	2003/01/24 11:50
-	5	813604.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/07 15:02



-	392	input near5 transistor near5 (match matching) near5 impedance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/07 15:20
-	13	(US-4200880-\$ or US-4004256-\$ or US-3942186-\$ or US-5387888-\$ or US-5371405-\$ or US-5696466-\$ or US-6348718-\$ or US-6501159-\$ or US-6479846-\$ or US-6455925-\$ or US-6331804-\$).did. or (US-20010004115-\$ or US-20020134993-\$).did.	USPAT; US-PGPUB	2003/07/07 15:20
-	13	((US-4200880-\$ or US-4004256-\$ or US-3942186-\$ or US-5387888-\$ or US-5371405-\$ or US-5696466-\$ or US-6348718-\$ or US-6501159-\$ or US-6479846-\$ or US-6455925-\$ or US-6331804-\$).did. or (US-20010004115-\$ or US-20020134993-\$).did.) and input near5 transistor near5 (match matching) near5 impedance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/07 15:23
-	13	((US-4200880-\$ or US-4004256-\$ or US-3942186-\$ or US-5387888-\$ or US-5371405-\$ or US-5696466-\$ or US-6348718-\$ or US-6501159-\$ or US-6479846-\$ or US-6455925-\$ or US-6331804-\$).did. or (US-20010004115-\$ or US-20020134993-\$).did.) and input near5 transistor near5 (match matching) near5 impedance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/07 17:05
-	48	impedance and matching (US-6177834-\$ or US-5880517-\$ or US-5696466-\$ or US-5539254-\$ or US-4042952-\$ or US-5387888-\$ or US-5492842-\$ or US-5563447-\$ or US-5519253-\$ or US-5444295-\$ or US-6501159-\$ or US-5973567-\$ or US-5552636-\$ or US-5446959-\$ or US-6331804-\$ or US-5982793-\$ or US-6479846-\$ or US-6455925-\$ or US-6348718-\$ or US-4200880-\$ or US-4004256-\$ or US-3942186-\$ or US-5371405-\$ or US-5023189-\$ or US-6281756-\$ or US-5576661-\$).did. or (US-5206608-\$).did. or (US-20020134993-\$ or US-20010038310-\$ or US-20010004115-\$).did. or (EP-680141-\$ or US-5206608-\$).did. or (JP-04218949-\$ or JP-07270443-\$ or JP-03114251-\$ or JP-05002316-\$ or JP-11238851-\$ or JP-06006150-\$ or JP-04321308-\$ or JP-02005459-\$ or JP-01199436-\$ or JP-01283951-\$ or JP-63086904-\$ or JP-55091148-\$ or JP-05218102-\$ or JP-2001024148-\$).did. or (EP-1237189-\$ or US-6177834-\$ or JP-01050602-\$).did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/08 07:55
-	5156	((438/10) or (438/11) or (438/13) or (438/14) or (438/17) or (438/18)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/08 07:58
-	7	((((438/10) or (438/11) or (438/13) or (438/14) or (438/17) or (438/18)).CCLS.) and (rf radio-frequency radio adj frequency) and impedance near12 match\$3 and wir\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/08 08:07
-	10407	impedance adj matching.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/08 08:07

-	263	substrate and (die or chip) and (wire wiring wires)and impedance adj matching.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/08 08:09
-	5	substrate and transistor and (die or chip) and (wire wiring wires)and impedance adj matching.ti,ab,clm. and ((step steps) near12 order)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/08 08:12
-	121	substrate and transistor and (die or chip) and (wire wiring wires)and impedance adj matching.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/08 08:54
-	0	substrate and transistor and (die or chip) and (wire wiring wires)and impedance adj matching.ti,ab,clm. and ("in" adj situ) near6 (test testing measuring measurement)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/08 08:55
-	0	substrate and transistor and (die or chip) and (wire wiring wires)and impedance adj matching.ti,ab,clm. and ("in" adj situ) near16 (test testing measuring measurement)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/08 08:55
-	0	("in" adj situ) near16 (test testing measuring measurement) same impedance adj matching	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/08 08:55
-	5161	((438/10) or (438/11) or (438/13) or (438/14) or (438/17) or (438/18)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/10 08:02
-	18	((((438/10) or (438/11) or (438/13) or (438/14) or (438/17) or (438/18)).CCLS.) and impedance near20 (match matching) and (wire wiring wires)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/10 08:05
-	3	((((438/10) or (438/11) or (438/13) or (438/14) or (438/17) or (438/18)).CCLS.) and impedance near20 (match matching) and (wire wiring wires) and transistor near20 (chip die)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/10 08:05